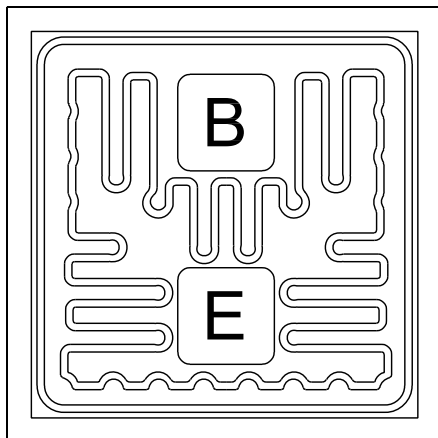


**PROCESS DETAILS**

Process	Epitaxial Planar
Die Size	18 x 18 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.8 x 3.8 MILS
Emitter Bonding Pad Area	3.8 x 3.8 MILS
Top Side Metalization	Al/Si - 30,000Å
Back Side Metalization	Au - 12,000Å

**GEOMETRY**



BACKSIDE COLLECTOR R0

**GROSS DIE PER 5 INCH WAFER**

54,330

**PRINCIPAL DEVICE TYPES**

CMLT3410  
CMPT3410  
CMST3410  
CMUT3410

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R0 (5- January 2006)